業績目録（坪内和夫）

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坪内和夫教授業績目録

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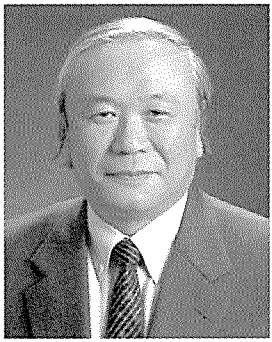

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学　　位

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受　　賞

昭和58年10月　服部報公賞
「窒化アルミニウムを用いた零温度係数弾性表面波素子の研究」
平成６年４月　第26回市村学術賞貢献賞

「超高信頼性無線通信技術：スペクトラム拡散通信モデムの開発」
平成８年３月　第11回電気通信普及財団賞（テレコムシステム技術賞）
平成９年７月　第22回井上春成賞
「超高信頼性スペクトラム拡散無線通信モデムの開発」
平成15年６月　平成15年度「電波の日」東北総合通信局長表彰
平成17年１月　2005年 FPGA/PLD Design Conference
ユーザプレゼンテーション審査員特別賞
「5GHz 帯 324Mbps 高速無線 LAN 端末開発におけるFPGA・実装設計（２）
～超高速 MAC 層処理 FPGA の設計～」
平成18年５月　平成17年度 電子情報通信学会業績賞
「スペクトル拡散通信モデムの開発と実用化」
平成19年６月　第５回産学官連携功労者表彰・文部科学大臣賞
「産学連携による次世代モバイルインターネット端末の開発」

社会・学会等における活動（役職等）

電子情報通信学会
スペクトル拡散研究会・委員　平成２年－平成５年
スペクトル拡散研究会・委員長　平成６年－平成９年
電子部品・材料研究専門委員会・委員　平成７年－平成８年
エレクトロニクスソサイエティ・副会長　平成９年－平成10年
「次世代 ULSI 科学的生産技術」英文論文小特集編集委員会・委員　平成７年－平成８年
応用物理学会
JJAP 編集委員会・編集委員　平成２年－平成９年
応用電子物性分科会・幹事　平成３年－平成５年
薄膜・表面物理分科会・委員　平成５年－平成10年
電気学会
半導体高性能プロセス調査専門委員会・幹事　昭和57年－昭和59年
微細加工プロセス調査委員会・幹事　昭和60年－昭和62年
超微細回路加工技術調査専門委員会・幹事　昭和63年－平成２年
超微細製造技術調査専門委員会・幹事　平成３年－平成５年
超微細プロセス調査専門委員会・委員　平成６年－平成９年
ULSI 用薄膜材料調査専門委員会・委員　平成７年－平成９年
電子デバイス技術委員会・委員　平成９年－
電子材料技術委員会・委員　平成９年－
プロセス・インテグレーション調査専門委員会・委員長　平成９年－平成11年
日本学術振興会
薄膜第131委員会・委員　平成５年－
弾性波素子第150委員会・委員　平成６年－
超集積化デバイス・システム第165委員会・委員　平成９年－
日本電子工業振興協会
電子材料技術委員会・委員　平成４年－平成９年
シリコン極限プロセス専門委員会・幹事　平成５年－平成６年
技術情報調査専門委員会・委員長　平成３年－平成４年

ポスト 0.1μm 技術と産業専門委員会・委員長　平成９年－平成10年
ワイヤレスシステムデバイス技術専門委員会・委員長　平成14年－平成15年
ワイヤレス通信センシングデバイス技術専門委員会・委員長　平成16年－平成17年
(財)未来工学研究所 調査研究「わが国における技術発展の方向性に関する調査」
エレクトロニクス分科会 プロジェクト研究委員会・委員　平成７年－平成９年
エレクトロニクス実装学会・理事　平成12年－平成13年
1995年度日本 IBM 賞・選考委員　平成７年
京都賞・先端技術部門・専門委員　平成17年
日本国際賞・情報通信の理論と技術部会・審査委員　平成20年
IEEE Electron Device Society, Tokyo Chapter,
Vice Chairperson　平成10年－平成11年
Chairperson　平成12年
Advanced Metallization and Interconnection Systems for ULSI Applications, Japan Session,
Committee Member　平成５年
Vice Chairperson　平成７年
Chairperson　平成８年－平成９年
Committee Member　平成10年
International Conference on Solid State Devices and Materials (SSDM),
Executive Committee Member　昭和62年－昭和63年
Executive Committee, Vice Chairperson　平成１年－平成２年
Program Committee Member　平成３年－平成５年
Executive Committee, Vice Chairperson　平成７年
Executive Committee, Vice Chairperson　平成10年
Program Committee, Chairperson　平成11年
Steering Committee, Chairperson　平成12年
Organizing Committee Member　平成13年
International Conference on Advanced Microelectronic Devices and Processings,
Executive Committee, Vice Chairperson　平成６年
First International Conference on Photo-Excited Process and Applications,
Committee Member　平成５年
The 7th International Conference on Vapor Phase Growth and Epitaxy,
Organizing Committee Member　平成３年
The 20th Personal, Indoor and Mobile Radio Communications Symposium 2009 (PIMRC'09)
General Co-Chair　平成21年

業　績　目　録

Ⅰ．著書・単行本所載論文

1. Non-Destructive and Noncontact Observation of Microdefects in GaAs Wafers with a New Photo-Thermal-Radiation (PTR) Microscope.
   Photoacoustic and Thermal Wave Phenomena in Semiconductors, (Edited by A. Mandelis), North-Holland, pp.53-65, (1987).
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3. スーパークリーンルームの省エネルギー設計と省エネルギー運転.
   LSI製造におけるプロセス高性能化技術(Ⅲ)，(大見忠弘，新田雄久監修)，リアライズ社，pp.133-162, (1989).
   大見忠弘，竹浪敏人，室田淳一，御子柴宣夫，坪内和夫，益　一哉

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   弾性波素子技術ハンドブック（日本学術振興会弾性表面波素子技術第150委員会編)，オーム社，pp.250-253, (1991).
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6. 光音響分光法.
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10. AlN 圧電膜：材料特性.
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